

No.1766C

2SA1407/2SC3601

PNP/NPN Epitaxial Planar Silicon Transistors

Ultrahigh-Definition CRT Display Video Output Applications

Applications

- · Ultrahigh-definition CRT display.
- · Video output.
- · Color TV chroma output.
- · Wide-band amp.

Features

- · High $f_T: f_T typ = 400MHz$.
- · High breakdown voltage: $V_{CEO} \ge 200V$.
- $\cdot \ Small \ reverse \ transfer \ capacitance \ and \ excellent \ high-frequency \ characteristic$
- : Cre = 2.0pF (NPN), 2.5pF (PNP).
- · Complementary PNP and NPN types.
- · Adoption of FBET process.

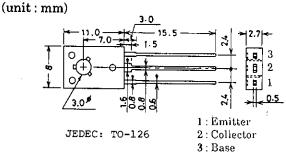
():2SA1407

Absolute Maximum Ratings at	ጥ _ን — 95°C			• .
				unit
Collector-to-Base Voltage	V_{CBO}		(-)200	V
Collector-to-Emitter Voltage	$ m V_{CEO}$		(-)200	V
Emitter-to-Base Voltage	V_{EBO}		(-)4	V
Collector Current	I_C		(-)150	$\mathbf{m}\mathbf{A}$
Collector Current (Pulse)	I_{CP}		(-)300	mA
Collector Dissipation	P_{C}		1.2	W
		$T_c = 25$ °C	7	W
Junction Temperature	Tj		150	$^{\circ}\mathrm{C}$
Storage Temperature	Tstg		-55 to +150	$^{\circ}\mathrm{C}$
Electrical Characteristics at Ta	=25°C		min typ	max unit
0.11	I_{CBO}	$V_{CB} = (-)150V, I_E = 0$	iiii cyp	(-)0.1 μA
79 • • • • • • • • • • • • • • • • • • •	IEBO	$V_{EB} = (-)2V_{,I_C} = 0$		$(-)1.0 \mu A$
		$V_{CE} = (-)10V, I_{C} = (-)10mA$	40※	320×
		$V_{CE} = (-)10V, I_{C} = (-)100mA$	20	0207.
~	f _T	$V_{CE} = (-)30V, I_{C} = (-)50mA$	400	MHz
	V _{CE(sat)}	$I_{C} = (-)50 \text{mA}, I_{R} = (-)5 \text{mA}$	400	0.6 V
	OE(SEL)	-C ()oomasiaB - ()outh		(-0.8)
			04:	•
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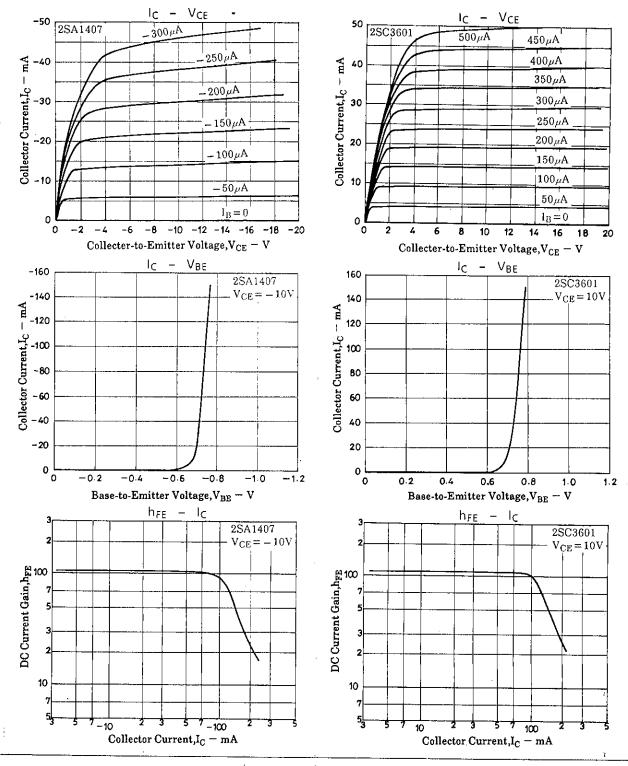
%: The 2SA1407/2SC3601 are classified by 10mA h_{FE} as follows.

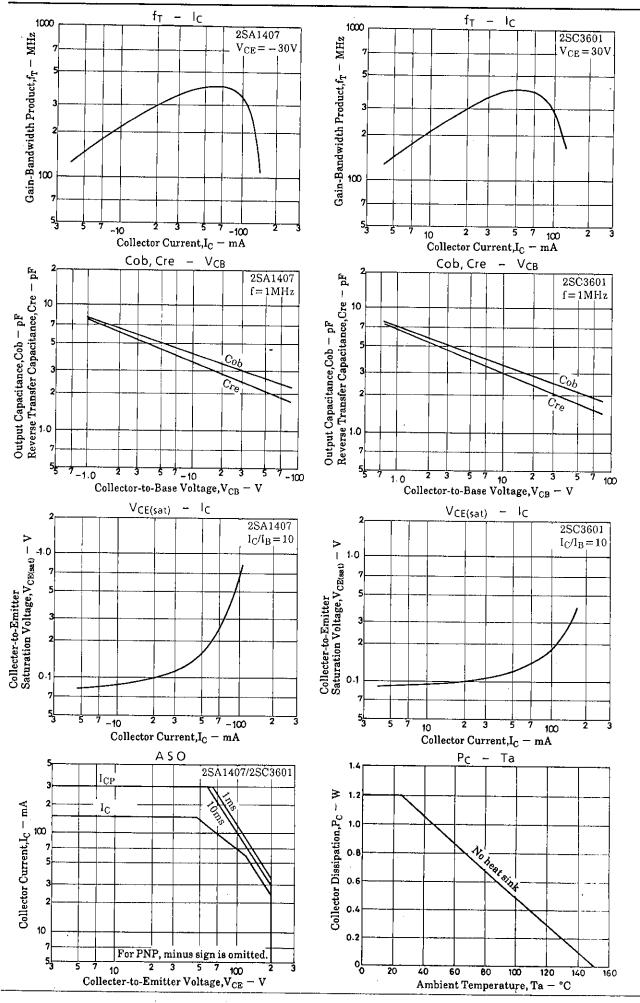
40	С	80	60	D	120	
100) E	200	160	F	320	

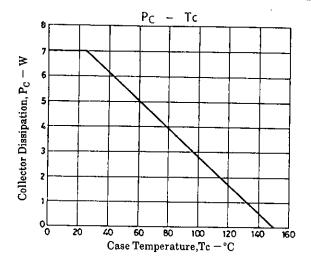
Package Dimensions 2009B



Continued from preceding page.			min	typ 1	max	unit
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = (-)50 \text{mA}, I_B = (-)5 \text{mA}$	******	V 1)1.0	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_{\rm C} = (-)10\mu A, I_{\rm E} = 0$	(-)200	`	,210	v
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)1 \text{mA}, R_{BE} = \infty$	(-)200			· v
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_{\rm E} = (-)100 \mu A, I_{\rm C} = 0$	(-)4			V
Output Capacitance	Cob	$V_{CB} = (-)30V, f = 1MHz$		2.5		рF
				(3.0)		рF
Reverse Transfer Capacitance	Cre	$V_{CB} = (-)30V, f = 1MHz$		2.0		pF
				(2.5)		pF







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This catalog provides information as of September, 1995. Specifications and information herein are subject to change without notice.



No.1973A

2SA1469/2SC3746

PNP/NPN Epitaxial Planar Silicon Transistors

60V/5A High-Speed Switching Applications

Applications

- · Various inductance lamp drivers for electrical equipment.
- · Inverters, converters (strobo, flash, fluorescent lamp lighting circuit).
- · Power amp (high power car stereo, motor controller).
- · High-speed switching (switching regulator, driver).

Features

- · Low saturation voltage.
- · Excellent current dependence of hFE.
- · Short switching time.
- · Micaless package facilitating mounting.

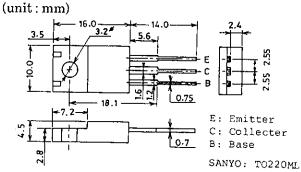
(): 2SA1469

Absolute Maximum Ratings	at $Ta = 25^\circ$	$^{\circ}\mathrm{C}$			unit	
Collector-to-Base Voltage	V_{CBO}			(-)80	V	
Collector-to-Emitter Voltage	V _{CEO}		((-)60	V	
Emitter-to-Base Voltage	V_{EBO}			(-)5	V	
Collector Current	${ m I}_{ m C}$			(-)5	Α	
Collector Current (Pulse)	${ m I_{CP}}$			(-)7	Α	
Collector Dissipation	${ m P}_{ m C}$			2	W	
		$Tc = 25^{\circ}C$		20	W	
Junction Temperature	Тj			150	$^{\circ}\mathrm{C}$	
Storage Temperature	Tstg		-55 to	+150	$^{\circ}\mathrm{C}$	
Electrical Characteristics at	Ta = 25°C		min	typ	max	unit
Collector Cutoff Current I	СВО	$V_{CB} = (-)40V, I_E = 0$			-)0.1	mA
D : a . a	EBO	$V_{EB} = (-)4V, I_C = 0$		-	-)0.1	mA
DC Current Gain h	FE	$V_{CE} = (-)2V, I_{C} = (-)1A$	70%	`	280%	
Gain-Bandwidth Product f	Γ	$V_{CE} = (-)5V, I_{C} = (-)1A$		100		MHz
C-E Saturation Voltage V	CE(sat)	$I_C = (-)2.5A, I_B = (-)0.125A$		(-	-)0.4	V
V . Di 00 A 1 400/000000			Cont	tinued o	n next	page.

%: The 2SA1469/2SC3746 are classified by 1A h_{FE} as follows

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1	70	Q	140	100	R	200	140	S	280

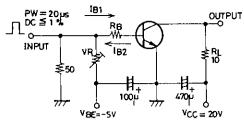
Package Dimensions 2041



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		•	min	typ	max	unit
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_{\rm C} = (-)1 {\rm mA}, I_{\rm E} = 0$	(-)80	• •		V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)1 \text{mA}, R_{BE} = \infty$	(-)60			v
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_{\rm E} = (-)1 {\rm mA}, I_{\rm C} = 0$	(-)5			V
Turn-on Time	t_{on}	See specified Test Circuit.		0.1		μS
Storage Time	$ m t_{stg}$	"		0.5		μS
Fall Time	t_f	"		0.1		μs

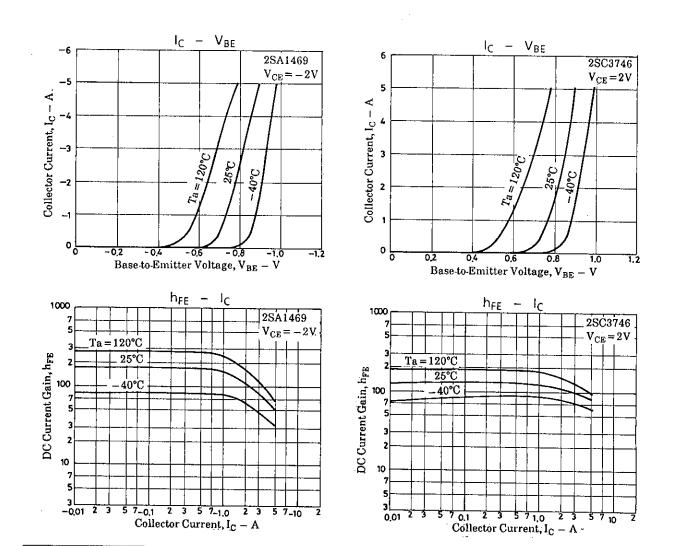
Switching Time Test Circuit

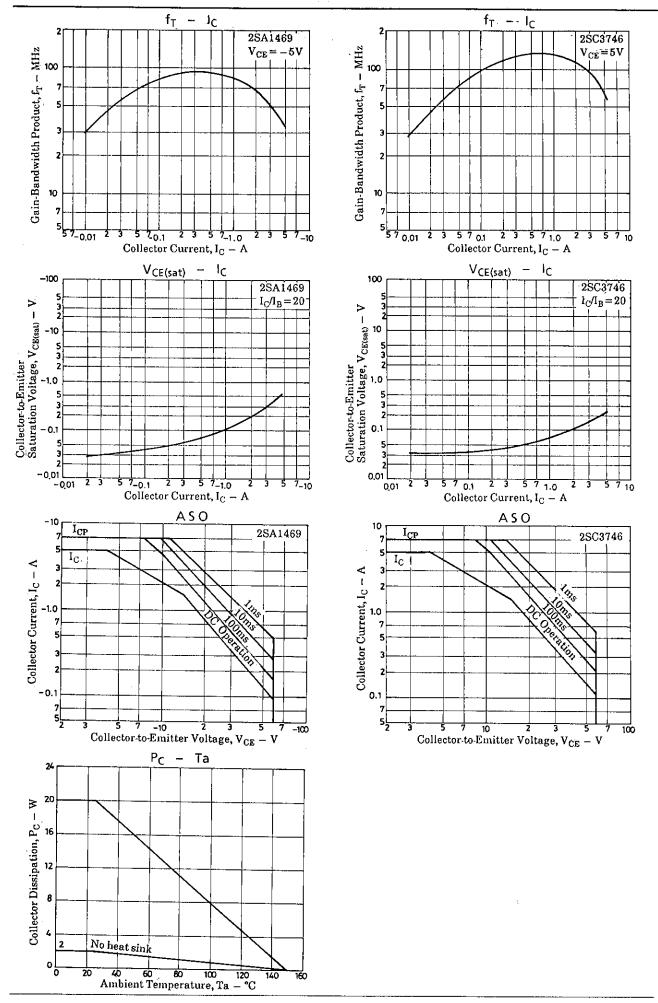


 $20I_B1 = -20I_B2 = I_C = 2A$

(For PNP, the polarity is reversed).

Unit (Resistance : Ω , Capacitance : F)





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